

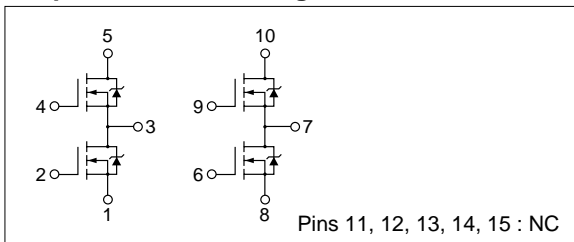
Absolute maximum ratings (Ta=25°C)

Symbol	Ratings	Unit
V _{DSS}	60	V
V _{GSS}	±20	V
I _D	5	A
I _{D(pulse)}	8 (PW≤1ms, Du≤25%)	A
P _T	4.8 (Ta=25°C, with all circuits operating, without heatsink)	W
	25 (Tc=25°C, with all circuits operating, with infinite heatsink)	
θ _{J-a}	26 (Junction-Air, Ta=25°C, with all circuits operating)	°C/W
θ _{J-c}	5 (Junction-Case, Tc=25°C, with all circuits operating)	°C/W
V _{ISO}	1000 (Between fin and lead pin, AC)	V _{rms}
T _{ch}	150	°C
T _{stg}	-40 to +150	°C

Electrical characteristics (Ta=25°C)

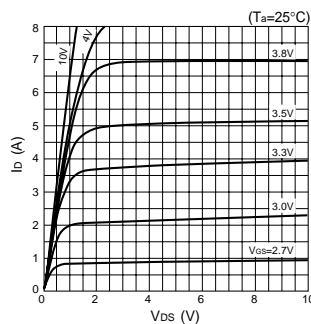
Symbol	Specification			Unit	Conditions
	min	typ	max		
V _{(BR)DSS}	60			V	I _D =100μA, V _{GS} =0V
I _{GSS}			±100	nA	V _{GS} =±20V
I _{DSS}			100	μA	V _{DS} =60V, V _{GS} =0V
V _{TH}	1.0		2.0	V	V _{DS} =10V, I _D =250μA
Re(yfs)		5.5		S	V _{DS} =10V, I _D =3A
R _{DS(ON)}			0.3	Ω	V _{GS} =4V, I _D =3A
C _{iss}		320		pF	V _{DS} =10V, f=1.0MHz, V _{GS} =0V
C _{oss}		160		pF	
C _{rss}		35		pF	
td(on)		16		ns	I _D =3A, V _{DD} ≐20V, R _L =6.67Ω, V _{GS} =5V, see Fig. 3 on page 16.
tr		65		ns	
td(off)		70		ns	
tf		45		ns	
V _{SD}		1.2		V	
t _{rr}		65		ns	I _{SD} =4A, V _{GS} =0V
					I _{SD} =3A, V _{GS} =0V, di/dt=100A/μs

Equivalent circuit diagram

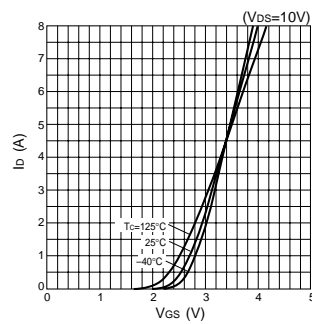


Characteristic curves

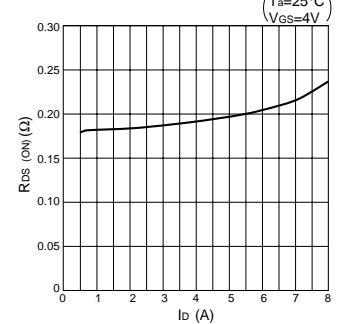
I_D-V_{DS} Characteristics (Typical)



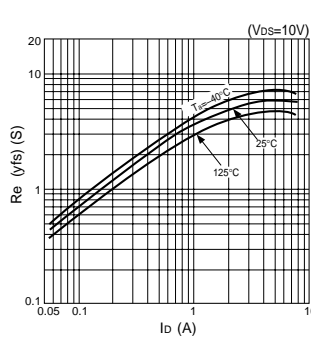
I_D-V_{GS} Characteristics (Typical)



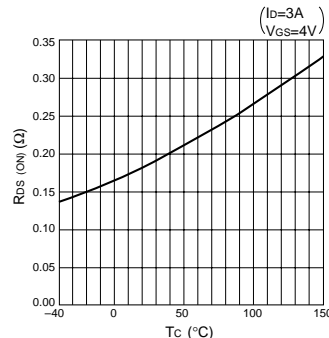
R_{DS(ON)}-I_D Characteristics (Typical)



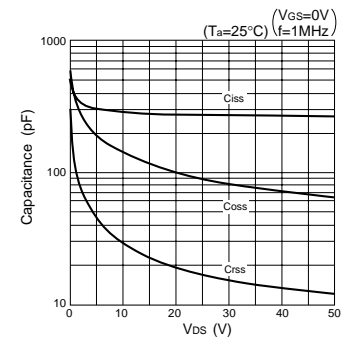
Re(yfs)-I_D Characteristics (Typical)



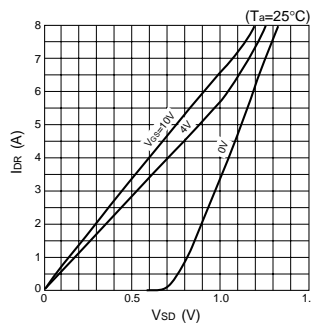
R_{DS(ON)}-T_C Characteristics (Typical)



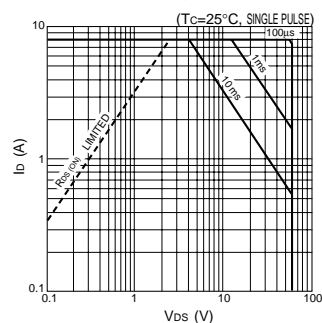
Capacitance-V_{DS} Characteristics (Typical)



I_{DR}-V_{SD} Characteristics (Typical)



Safe Operating Area (SOA)



P_T-T_a Characteristics

